

isc Silicon NPN Power Transistor

2SC6017

DESCRIPTION

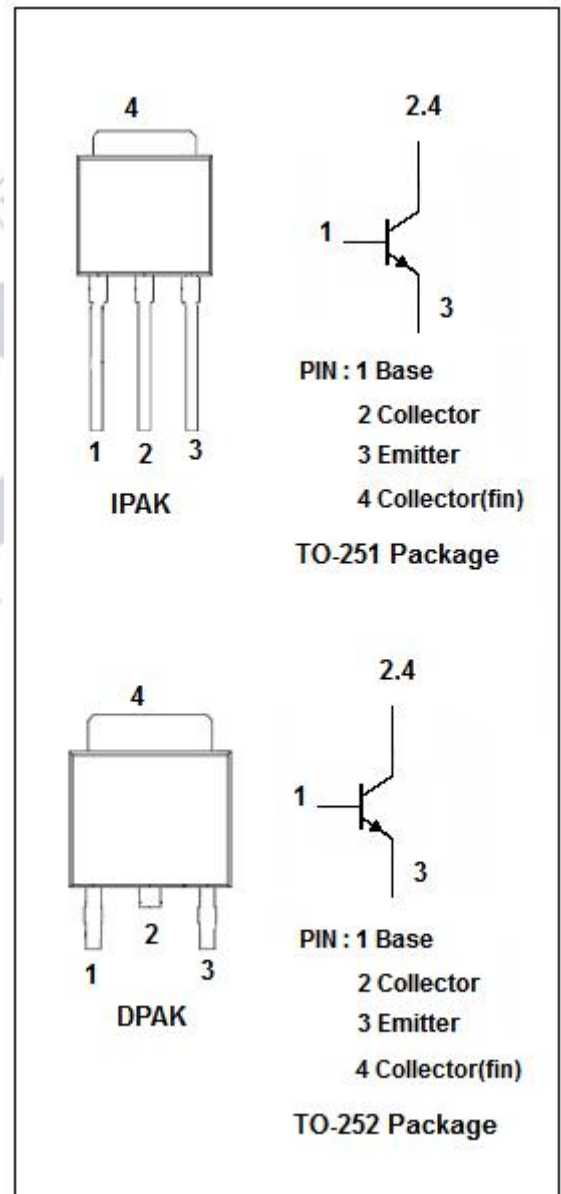
- Large current capacitance
- High-speed switching
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation
- Complementary to 2SA2169

APPLICATIONS

- relay drivers, lamp drivers, motor drivers

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	10	A
I_{CM}	Collector Current-Peak	13	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	20	W
	Collector Power Dissipation @ $T_a=25^{\circ}\text{C}$	0.95	
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



isc Silicon NPN Power Transistor**2SC6017****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 250mA			0.36	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 250mA			1.4	V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA; I _B = 0	50			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 100uA; I _C = 0	6			V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40V; I _E = 0			10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0			10	μ A
h _{FE}	DC Current Gain	I _C = 1A; V _{CE} = 2V	200		700	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1.0MHz		60		pF
f _T	Current-Gain—Bandwidth Product	I _C = 1A; V _{CE} = 5V		200		MHz

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Outline Drawing

